

# SEMICONDUCTORS-DISCRETES

PartNo.	ProductNo.	Manuf.	Description	N/P	Vdss(max.)	Rds(on)(max)	Pd(max)	Id(max)	Pins/Package
22019	SI4431	Fairchild	Logic Level Enhancement Mode Field Effect Transistor	P-Ch	-30V	0.029	2.5W	±5.8A	8P/SO-8
18525	SSH11N90	Fairchild	N-Channel MOSFET	N	900V			11A	3P/TO-3P
18527	SSH5N90A	Fairchild	N-Channel MOSFET	N	900V			5A	3P/TO-3P
18526	SSH6N90A	Fairchild	N-Channel MOSFET	N	900V			6A	3P/TO-3P
15672	SSP1N60B	Fairchild	N-channel MOSFET	N-Ch.	600V	12		1A	3P/TO-220
18529	SSP6N60A	Fairchild	N-Channel MOSFET	N	600V			6A	3P/TO-220
18530	SSP6N80	ST(SGS)	N-Channel MOSFET	N	800V			6A	3P/TO-220
22842	STP20NM50	ST(SGS)	Power MOSFET	N-Ch.	500V		0.25W	20A	3P/TO-220
14502	STP55NE06	ST(SGS)	N-CHANNEL MOSFET	N	60V	0.018	130W	55A	3P/TO-220
19583	TPC8301	TOSHIBA	Silicon P Channel MOS Type (L2- -MOSVI)	P	-30V	190	1.5W	-3.5A	8P/2-6J1E
23014	VN10KLS	VISHAY	N-Channel 60-V (D-S) MOSFETs with Zener Gate	N	60V	5 @ VGS=10V	0.9W/TA=25	0.31A	3P/TO-92S
27086	VN50300T	VISHAY	N-Channel 500-V (D-S) MOSFETs	N	500V	0.022	0.35W	240	3P/TO-236(SOT-23)

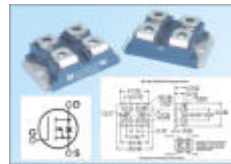
## 功率場效模塊 PowerMosfetModuies

詳細產品規格--請點擊[www.100y.com.tw](http://www.100y.com.tw)



TE53N50E

**FEATURES:**  
Faster Switching  
100% Avalanche Tested  
Lower Leakage  
Popular SOT-227 Package

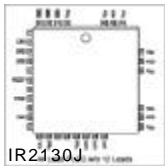


SOT-227

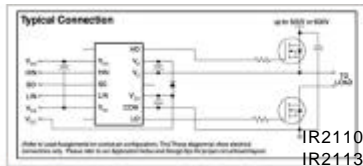
PartNo.	ProductNo.	Manuf.	Description	Vdss(max.)	Rds(on)	Pd(max)	Id(Cont.)	Pins/Package
16557	APT10025JVR	APT	Power MOSFET 模塊	1000V	0.25	700W	34A	SOT-227
17626	APT10050JN	APT	Power MOSFET 模塊	1000V	0.50	520W	20.5A	SOT-227
21941	TE53N50E	MOT.	Power MOSFET 模塊	500V		400W	53A	

## IGBT和MOSFET驅動IC MOSFET/IGBT-Drivers

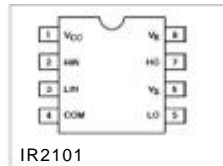
詳細產品規格--請點擊[www.100y.com.tw](http://www.100y.com.tw)



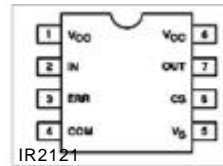
IR2130J



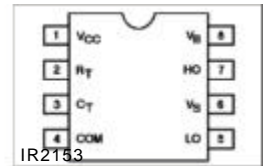
IR2110  
IR2113



IR2101



IR2121

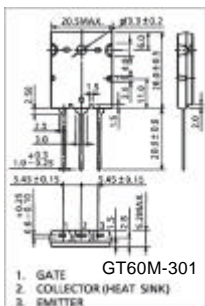


IR2153

PartNo.	ProductNo.	Manuf.	Description	Vss	Ic	Tr/ns	Tf/ns	Package
15673	IR2101	IR	HIGH AND LOW SIDE DRIVER	20V	100mA	100	130	8P/DIP
13260	IR2110	IR	HIGH AND LOW SIDE DRIVER	500V	2A	120	94	14P/DIP
23348	IR2110S	IR	HIGH AND LOW SIDE DRIVER	-25~0.3V	2A	35ns	25ns	16P/SOIC
16069	IR2112	IR	HIGH AND LOW SIDE DRIVER			125	105	14P/DIP
17941	IR2113	IR	HIGH AND LOW SIDE DRIVER	600V	20A		94	14P/DIP
16064	IR2121	IR	CURRENT LIMITING LOW SIDE DRIVER	600V	1A	150	150	8P/DIP
13219	IR2130	IR	3-PHASE BRIDGE DRIVER	20V	0.5A	675	425	28P/DIP
16065	IR2130J	IR	3-PHASE BRIDGE DRIVER		420mA	675	425	44P/PCLL
15674	IR2151	IR	Self-oscillating Half-bridge Driver	600V	210mA	80	40	8P/DIP
13341	IR2152S	IR	Self-oscillating Half-bridge Driver	600V	100mA/210mA	80ns	40ns	8P/SOIC
16492	IR2153	IR	Self-oscillating Half-bridge Driver	600V		80	40	8P/DIP
28098	TC4403CPA	MICRO-CHIP	HIGH-SPEED FLOATING LOAD DRIVER	22V	1.5A	23	25	8P/DIP

## IGBT 晶體 IGBT Discrete

詳細產品規格--請點擊[www.100y.com.tw](http://www.100y.com.tw)



GT60M-301

**HIGH POWER SWITCHING APPLICATIONS**  
The 3rd Generation  
FRD Included Between Emitter and Collector  
Enhancement-Mode  
High Speed  $I_{GBT} = 0.25 \mu s$  (Typ.)  
FRD:  $t_f = 0.7 \mu s$  (Typ.)  
Low Saturation Voltage:  $V_{CE(sat)} = 3.4V$  (Max.)



BUP307 BUP314

**IGBT Preliminary data**  
Low forward voltage drop  
High switching speed  
Low tail current  
Latch-up free  
Avalanche rated

PartNo.	ProductNo.	Manuf.	Description	Pd(max)/W	Vces	Ic(A)	Pins/Package
17918	BUP307	SIEMENS	IGBT		1200V	35A	TO-218AB
20239	BUP314	SIEMENS	IGBT				TO-3P(TO-218AB)
10245	GT60M-301	TOSHIBA	IGBT		900V	60A	3P/TO-264
23946	GT60M303	TOSHIBA	IGBT		900V	60A	TO-3P
22284	HGTP3N60C3D	HARRIS	IGBT with Anti-Parallel Hyperfast Diodes	33W	600V	6A	TO-220AB

